

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims:

Listing of Claims:

1-2. (Canceled)

3. (Original) A semiconductor light emitting device, comprising a substrate, and at least two or more mesa portions in each of which a first semiconductor layer, an active layer and a second semiconductor layer that are sequentially provided on the substrate,

wherein the second semiconductor layers have a polarity different from that of the first semiconductor layers and further the second semiconductor layers and the active layers are spatially separated between the mesa portions.

4-5. (Canceled)

6. (Currently amended) The semiconductor light emitting device according to ~~any one of claims 2 to 4~~ claim 3,

wherein a total area of the first semiconductor layer, the active layer and the second semiconductor layer in side faces where the active layer is uncovered is 5% or more of an area of an uncovered upper face at a side of the second semiconductor layer.

7. (Currently amended) The semiconductor light emitting device according to ~~any one of claims 3 to 5~~ claim 3,

wherein a shortest distance from all points contained in the active layer to side faces where the active layer is uncovered is 40 μm or less.

8-9. (Canceled)

10. (Currently amended) The semiconductor light emitting device according to ~~any one of claims 1 to 5~~ claim 3,

wherein a face of the substrate opposite to a face of the substrate where the first semiconductor layer is formed has a reflecting layer.

11. (Currently amended) The semiconductor light emitting device according to ~~any one of claims 1 to 5~~ claim 3,

which is a group III Nitride Compound Semiconductor light emitting device represented by $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}$ wherein ($0 \leq x \leq 1$, $0 \leq y \leq 1$, and $0 \leq x + y \leq 1$).

12. (Canceled)

13. (Currently amended) The semiconductor light emitting device according to ~~any one of claims 3 and 4~~ claim 3,

wherein a shape of an uncovered upper face at a side of the second semiconductor layer has an apex having an angle of less than 45 degrees.

14. (Currently amended) The semiconductor light emitting device according to ~~any one of claims 3 and 4~~ claim 3,

wherein one of interior angles made by side faces where the active layer is uncovered and an uncovered upper face at a side of the second semiconductor layer is 138 degrees or more.